

HIGH SPEED 2K x 8 DUAL PORT STATIC RAM

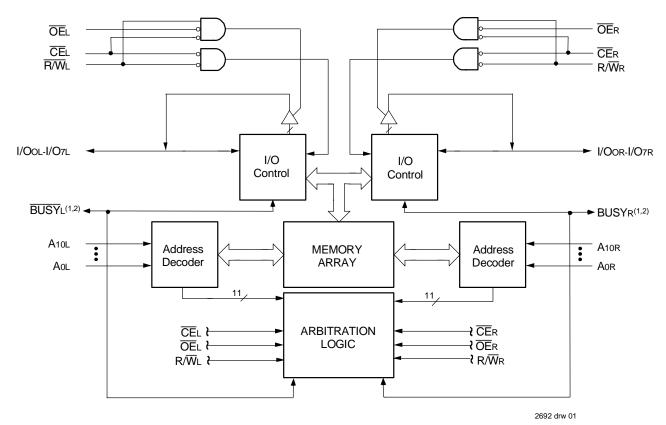
IDT7132SA/LA IDT7142SA/LA

Features

- High-speed access
 - Commercial: 20/25/35/55/100ns (max.)
 - Industrial: 25ns (max.)
 - Military: 25/35/55/100ns (max.)
- Low-power operation
 - IDT7132/42SA
 - Active: 325mW (typ.)
 - Standby: 5mW (typ.)
 - IDT7132/42LA
 - Active: 325mW (typ.) Standby: 1mW (typ.)

- MASTER IDT7132 easily expands data bus width to 16-or-more bits using SLAVE IDT7142
- On-chip port arbitration logic (IDT7132 only)
- ♦ BUSY output flag on IDT7132; BUSY input on IDT7142
- ◆ Battery backup operation —2V data retention (LA only)
- ◆ TTL-compatible, single 5V ±10% power supply
- Available in 48-pin DIP, LCC and Flatpack, and 52-pin PLCC packages
- Military product compliant to MIL-PRF-38535 QML
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Green parts available, see ordering information

Functional Block Diagram



NOTES:

- IDT7132 (MASTER): BUSY is open drain output and requires pullup resistor of 270Ω. IDT7142 (SLAVE): BUSY is input.
- 2. Open drain output: requires pullup resistor of 270Ω .

JANUARY 2006

Description

The IDT7132/IDT7142 are high-speed 2K x 8 Dual-Port Static RAMs. The IDT7132 is designed to be used as a stand-alone 8-bit Dual-Port RAM or as a "MASTER" Dual-Port RAM together with the IDT7142 "SLAVE" Dual-Port in 16-bit-or-more word width systems. Using the IDT MASTER/ SLAVE Dual-Port RAM approach in 16-or-more-bit memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

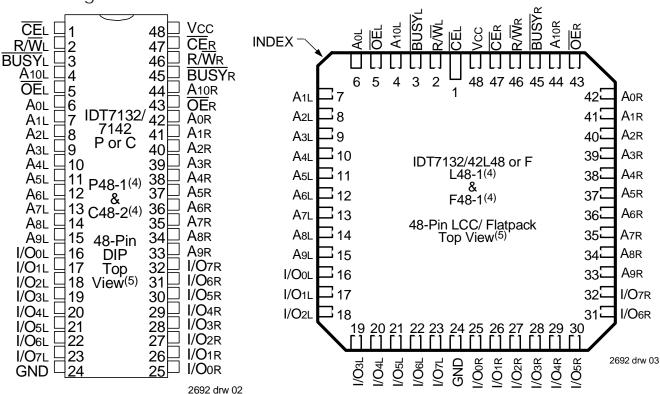
Both devices provide two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by $\overline{\text{CE}}$ permits the on-chip circuitry of each port to enter

a very low standby power mode.

Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 325mW of power. Low-power (LA) versions offer battery backup data retention capability, with each Dual-Port typically consuming 200µW from a 2V battery.

The IDT7132/7142 devices are packaged in a 48-pin sidebraze or plastic DIPs, 48-pin LCCs, 52-pin PLCCs, and 48-lead flatpacks. Military grade product is manufactured in compliance with the latest revision of MIL-PRF-38535 QML, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

Pin Configurations^(1,2,3)



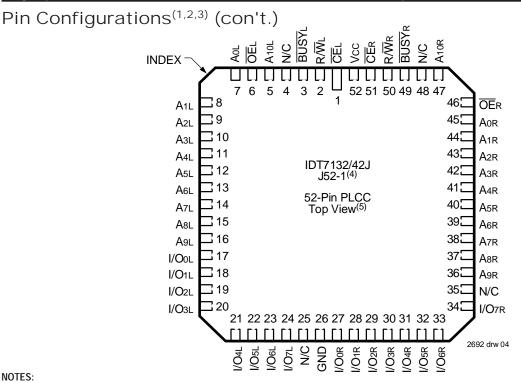
NOTES:

- All Vcc pins must be connected to the power supply.
- 2. All GND pins must be connected to the ground supply.
- 3. P48-1 package body is approximately .55 in x 2.43 in x .18 in. C48-2 package body is approximately .62 in x 2.43 in x .15 in. L48-1 package body is approximately .57 in x .57 in x .68 in. F48-1 package body is approximately .75 in x .75 in x .11 in.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Capacitance⁽¹⁾ (TA = +25°C,f = 1.0MHz)

Symb	ol	Parameter	Conditions ⁽²⁾	Max.	Unit
CIN		Input Capacitance	VIN = 3dV	11	pF
Cou	Т	Output Capacitance	Vout = 3dV	11	pF
					2692 thl 00

- This parameter is determined by device characterization but is not production tested.
- 3dV represents the interpolated capacitance when the input and output signals switch from 3V to 0V.



NOTES:

- 1. All Vcc pins must be connected to the power supply.
- 2. All GND pins must be connected to the ground supply.
- 3. Package body is approximately .75 in x .75 in x .17 in.
- 4. This package code is used to reference the package diagram.
- This text does not indicate orientation of the actual part-marking

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Military	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
TSTG	Storage Temperature	-65 to +150	-65 to +150	°C
ЮЛ	DC Output Current	50	50	mA

2692 tbl 01 NOTES:

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq Vcc + 10%.

Recommended Operating Temperature and Supply Voltage (1,2)

Grade	Ambient Temperature	GND	Vcc
Military	-55°C to+125°C	0V	5.0V <u>+</u> 10%
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

2692 tbl 02

- NOTES:
- 1. This is the parameter Ta. This is the "instant on" case temperature.
- 2. Industrial temperature: for specific speeds, packages and powers contact your

Recommended DC Operating Conditions

Symbol	Parameter	Parameter Min. Typ.		Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
VIH	Input High Voltage	2.2	_	6.0(2)	V
VIL	Input Low Voltage	-0.5 ⁽¹⁾	_	0.8	V

2692 tbl 03

- NOTES:
- VIL (min.) = -1.5V for pulse width less than 10ns.
- VTERM must not exceed Vcc + 10%.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(1,5,8) (Vcc = 5.0V ± 10%)

7132X20⁽²⁾ 7132X25⁽⁷⁾ 7132X35 7142X20⁽²⁾ 7142X25⁽⁷⁾ 7142X35 Com'l Only Com'l, Ind Com'l & & Military Military **Test Condition** Version Max. Unit Symbol Parameter Тур. Тур. Тур. Dynamic Operating Current (Both Ports Active) $\overline{CE}L = \overline{CE}R = VIL$, Outputs Disabled $f = fMAX^{(3)}$ COM'L 110 ICC 110 250 80 165 mΑ 220 110 MIL & SA 110 230 280 80 IND LA 110 220 80 170 Standby Current (Both Ports - TTL $\overline{CE}L = \overline{CER} = VIH,$ COM'L SA LA 30 30 65 45 ISB1 30 30 65 45 25 25 mΑ 65 45 $f = fMAX^{(3)}$ Level Inputs) MIL & 30 30 80 60 SA 80 25 25 IND LA 60 \overline{CE} "A" = VIL and \overline{CE} "B" = VIH⁽⁶⁾ Standby Current (One Port - TTL COM'L SA LA 165 125 150 115 125 90 ISB2 65 65 65 50 50 mΑ Active Port Outputs Disabled f=fMAX⁽³⁾ 65 Level Inputs) MIL & SA 65 160 50 150 IND 50 LA 65 125 115 $\overline{\text{CE}}\text{L}$ and $\overline{\text{CE}}\text{R} \ge \text{VCC}$ -0.2V VIN $\ge \text{VCC}$ -0.2V or VIN $\le \text{0.2V}$, f = 0⁽⁴⁾ ISB3 Full Standby Current (Both COM'L 1.0 15 1.0 15 Ports - All CMOS Level Inputs) LA 0.2 0.2 0.2 MIL & 1.0 30 1.0 30 IND LA 0.2 10 0.2 10 $\begin{array}{l} \overline{\text{CE}}\text{-}\text{R}^* \leq 0.2 V \text{ and } \overline{\text{CE}}\text{-}\text{B}^* \geq V\text{CC} - 0.2 V^{(6)} \\ V\text{IN} \geq V\text{CC} - 0.2 V \text{ or } V\text{IN} \leq 0.2 V \\ \text{Active Port Outputs Disabled} \\ f = f\text{MAX}^{(3)} \end{array}$ Full Standby Current COM'L SA 60 155 60 145 45 110 ISB4 mΑ (One Port - All 60 115 105 45 CMOS Level Inputs) MIL & 155 115 45 SA 60 145 45

2692 tbl 04b

				7132X55 7142X55 Com'l & Military		2X55 n'l &	7142 Con	X100 X100 n'l & itary	
Symbol	Parameter	Test Condition	Versi	on	Тур.	Max.	Тур.	Max.	Unit
Icc	Dynamic Operating Current (Both Ports Active)	CEL = CER = VIL, Outputs Disabled f = fMAX ⁽ⁱ⁾	COM'L	SA LA	65 65	155 110	65 65	155 110	mA
	(Built Fulls Active)	I = IMAX*/	MIL & IND	SA LA	65 65	190 140	65 65	190 140	
ISB1	Standby Current (Both Ports - TTL Level Inputs)	$\overline{CE}L = \overline{CE}R = VIH,$ $f = fMAX^{(S)}$	COM'L	SA LA	20 20	65 35	20 20	55 35	mA
	Level inputs)		MIL & IND	SA LA	20 20	65 45	20 20	65 45	
ISB2	Standby Current (One Port - TTL	CEA* = VIL and CEB* = VIH(6) Active Port Outputs Disabled	COM'L	SA LA	40 40	110 75	40 40	110 75	mA
	Level Inputs)	f=fmax ⁽⁵⁾	MIL & IND	SA LA	40 40	125 90	40 40	125 90	
ISB3	Full Standby Current (Both Ports - All	\overline{CE} L and \overline{CE} R \geq VCC -0.2V VIN \geq VCC -0.2V or VIN \leq 0.2V, f = 0 ⁽⁴⁾	COM'L	SA LA	1.0 0.2	15 4	1.0 0.2	15 4	mA
	CMOS Level Inputs)		MIL & IND	SA LA	1.0 0.2	30 10	1.0 0.2	30 10	
ISB4	Full Standby Current (One Port - All	\overline{CE} 'A" \leq 0.2V and \overline{CE} 'B" \geq VCC -0.2V ⁽⁶⁾ VN \geq VCC - 0.2V or VN \leq 0.2V	COM'L	SA LA	40 40	100 70	40 40	95 70	mA
	Civios Level inputs)	OS Level Inputs) Active Port Outputs Disabled $f = f_{MAX}^{(i)}$	MIL & IND	SA LA	40 40	110 85	40 40	110 80	

- 1. 'X' in part numbers indicates power rating (SA or LA).
- 2. PLCC Package only
- 3. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc, and using "AC TEST CONDITIONS" of input levels of GND to 3V.
- 4. f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby.
- 5. Vcc = 5V, $Ta=+25^{\circ}C$ for Typ and is not production tested. $Vcc \ DC = 100mA$ (Typ)
- 6. Port "A" may be either left or right port. Port "B" is opposite from port "A".
- 7. Not available in DIP packages.
- 8. Industrial temperature: for specific speeds, packages and powers contact your sales office.

DC Electrical Characteristics Over the Operating

Temperature Supply Voltage Range (Vcc = 5.0V ± 10%)

			7132SA 7142SA				
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
ILI	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, Vin = 0V to Vcc	-	10	1	5	μA
ILO	Output Leakage Current	$\frac{\text{Vcc}}{\text{CE}} = 5.5\text{V},$ $\frac{\text{CE}}{\text{CE}} = \text{ViH}, \text{ Vout} = 0\text{V to Vcc}$		10		5	μA
Vol	Output Low Voltage	IoL = 4mA	_	0.4	_	0.4	٧
Vol	Open Drain Output Low Voltage (BUSY)	IoL = 16mA		0.5	_	0.5	V
Vон	Output High Voltage	Iон = -4mA	2.4	_	2.4	_	V

2692 tbl 05

2692 tbl 06

NOTE:

1. At $Vcc \le 2.0V$ leakages are undefined.

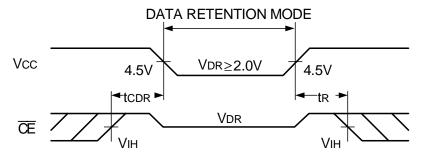
Data Retention Characteristics (LA Version Only)

Symbol	Parameter	Test Condition	Min.	Typ. ⁽¹⁾	Мах.	Unit	
VDR	Vcc for Data Retention	Vcc = 2.0V		2.0	1	1	V
ICCDR	Data Retention Current	CE ≥ Vcc -0.2V	Mil. & Ind.	-	100	4000	μA
		VIN > Vcc -0.2V or	Com'l.	_	100	1500	μΑ
tcdr ⁽³⁾	Chip Deselect to Data Retention Time	VIN <u><</u> 0.2V		0	_	_	ns
tR ⁽³⁾	Operation Recovery Time			trc ⁽²⁾	_	_	ns

NOTES:

- 1. Vcc = 2V, TA = +25°C, and is not production tested.
- 2. trc = Read Cycle Time
- 3. This parameter is guaranteed but not production tested.

Data Retention Waveform



2692 drw 05

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1, 2, and 3

2692 tbl 07

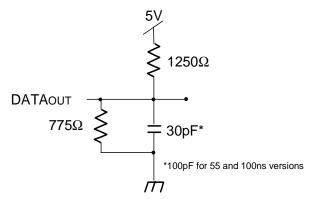


Figure 1. AC Output Test Load

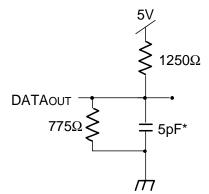


Figure 2. Output Test Load (for thz, t\text{tz, twz, and tow)} * Including scope and jig

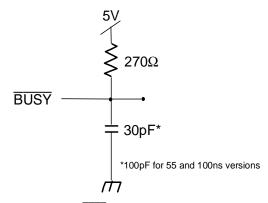


Figure 3. BUSY AC Output Test Load

2692 drw 06

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(3,5)

•		7132X20 ⁽²⁾ 7142X20 ⁽²⁾ Com'l Only		7142X20 ⁽²⁾		7142X20 ⁽²⁾		7142X20 ⁽²⁾		7142X20 ⁽²⁾		7142X20 ⁽²⁾ 7 Com'l Only C		7142 Com	2X25 ⁽²⁾ 7132X35 2X25 ⁽²⁾ 7142X35 1'l, Ind Com'l & ilitary Military		2X35 n'I &	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit										
READ CYC	CLE																	
trc	Read Cycle Time	20	_	25	_	35	1	ns										
taa	Address Access Time	-	20	_	25		35	ns										
t ace	Chip Enable Access Time		20		25		35	ns										
taoe	Output Enable Access Time		11	_	12	_	20	ns										
tон	Output Hold from Address Change	3		3		3		ns										
tLZ	Output Low-Z Time ^(1,4)	0		0		0		ns										
tHZ	Output High-Z Time ^(1,4)		10	_	10		15	ns										
tpu	Chip Enable to Power Up Time (4)	0	_	0	_	0	_	ns										
tpD	Chip Disable to Power Down Time ⁽⁴⁾	_	20		25	_	35	ns										

2692 tbl 08a

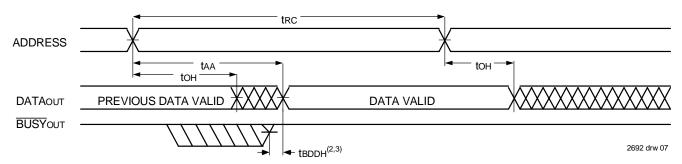
		7132X55 7142X55 Com'l & Military		7142X55 Com'l &		7132X100 7142X100 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit		
READ CYC	CLE							
trc	Read Cycle Time	55	-	100	-	ns		
taa	Address Access Time		55		100	ns		
tace	Chip Enable Access Time		55		100	ns		
taoe	Output Enable Access Time	_	25	-	40	ns		
tон	Output Hold from Address Change	3		10		ns		
tLZ	Output Low-Z Time ^(1,4)	5		5	-	ns		
tHZ	Output High-Z Time ^(1,4)	_	25		40	ns		
tpu	Chip Enable to Power Up Time ⁽⁴⁾	0	_	0	-	ns		
tpD	Chip Disable to Power Down Time ⁽⁴⁾	_	50		50	ns		

NOTES

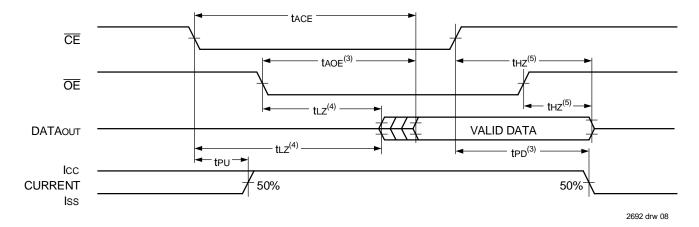
- 1. Transition is measured 0mV from Low or High-Impedance Voltage Output Test Load (Figure 2).
- 2. PLCC package only.
- 3. 'X' in part numbers indicates power rating (SA or LA).
- 4. This parameter is guaranteed by device characterization, but is not production tested.
- 5. Industrial temperature: for specific speeds, packages and powers contact your sales office.

2692 tbl 08b

Timing Waveform of Read Cycle No. 1, Either Side⁽¹⁾



Timing Waveform of Read Cycle No. 2, Either Side⁽¹⁾



- 1. $R\overline{N} = V_{IH}$, $\overline{CE} = V_{IL}$, and is $\overline{OE} = V_{IL}$. Address is valid prior to the coincidental with \overline{CE} transition LOW.
- 2. tbbb delay is required only in the case where the opposite port is completing a write operation to the same address location. For simultaneous read operations, BUSY has no relationship to valid output data.
- 3. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA, and tBDD.
- 4. Timing depends on which signal is asserted last, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 5. Timing depends on which signal is de-asserted first, $\overline{\sf OE}$ or $\overline{\sf CE}$.

AC Electrical Characteristics Over the Operating Temperature Supply Voltage Range^(5,6)

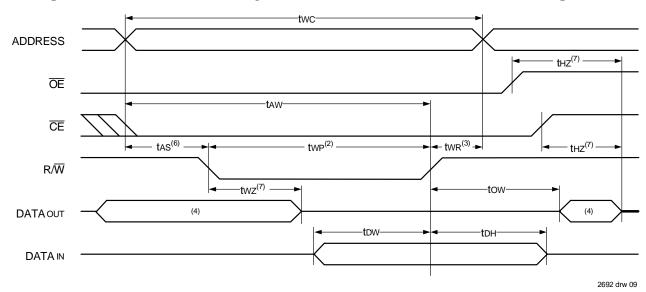
	The removator of capping vertage	7132X20 ⁽²⁾ 7142X20 ⁽²⁾ Com'l Only		7142X20 ⁽²⁾		7142X20 ⁽²⁾		7142X20 ⁽²⁾		7132X25 ⁽²⁾ 7142X25 ⁽²⁾ Com'l, Ind & Military		7132X35 7142X35 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max	Min.	Max.	Unit						
WRITE CYCLE														
twc	Write Cycle Time ⁽³⁾	20	_	25	_	35		ns						
tew	Chip Enable to End-of-Write	15	_	20		30		ns						
taw	Address Valid to End-of-Write	15		20	-	30		ns						
tas	Address Set-up Time	0		0		0		ns						
twp	Write Pulse Width ⁽⁴⁾	15	_	15		25		ns						
twr	Write Recovery Time	0	_	0		0		ns						
tow	Data Valid to End-of-Write	10		12		15		ns						
tHZ	Output High-Z Time ⁽¹⁾	_	10	_	10	-	15	ns						
tон	Data Hold Time	0	_	0	_	0		ns						
twz	Write Enable to Output in High-Z ⁽¹⁾	_	10		10	_	15	ns						
tow	Output Active from End-of-Write ⁽¹⁾	0	_	0	_	0		ns						

2692 tbl 09

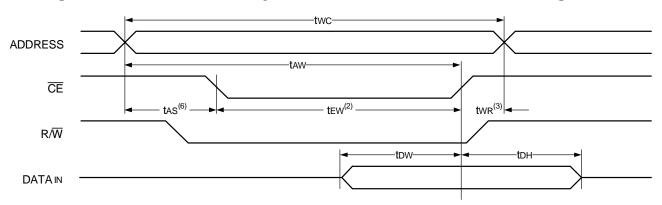
		7142 Con	2X55 2X55 n'l & tary	7132X100 7142X100 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE						
twc	Write Cycle Time ⁽³⁾	55	_	100	_	ns
tew	Chip Enable to End-of-Write	40	_	90		ns
taw	Address Valid to End-of-Write	40	_	90		ns
tas	Address Set-up Time	0		0	-	ns
twp	Write Pulse Width ⁽⁴⁾	30		55		ns
twr	Write Recovery Time	0		0		ns
tow	Data Valid to End-of-Write	20	_	40		ns
tHZ	Output High-Z Time ⁽¹⁾	_	25	_	40	ns
tон	Data Hold Time	0	_	0		ns
twz	Write Enable to Output in High-Z ⁽¹⁾	_	30	_	40	ns
tow	Output Active from End-of-Write ⁽¹⁾	0	_	0	_	ns

- 1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2). This parameter is guaranteed by device characterization but is not production tested.
- 2. PLCC package only.
- 3. For Master/Slave combination, two = tbaa + twp, since R/W = VIL must occur after tbaa.
- 4. If \overline{OE} is LOW during a $R\overline{W}$ controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If \overline{OE} is High during a $R\overline{W}$ controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 5. 'X' in part numbers indicates power rating (SA or LA).
- 6. Industrial temperature: for specific speeds, packages and powers contact your sales office.

Timing Waveform of Write Cycle No. 1, (R/W Controlled Timing)(1,5,8)



Timing Waveform of Write Cycle No. 2, (**CE** Controlled Timing)^(1,5)



NOTES: 2692 drw 10

- R/W or CE must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of $\overline{\text{CE}}$ = VIL and $\overline{\text{RW}}$ = VIL.
- 3. two is measured from the earlier of $\overline{\text{CE}}$ or $\overline{\text{RW}}$ going HIGH to the end of the write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE LOW transition occurs simultaneously with or after the R/W LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal (CE or R/W) is asserted last.
- 7. This parameter is determined be device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If \widetilde{OE} is LOW during a \widetilde{RW} controlled write cycle, the write pulse width must be the larger of two or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If \widetilde{OE} is HIGH during a \widetilde{RW} controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(7,8)

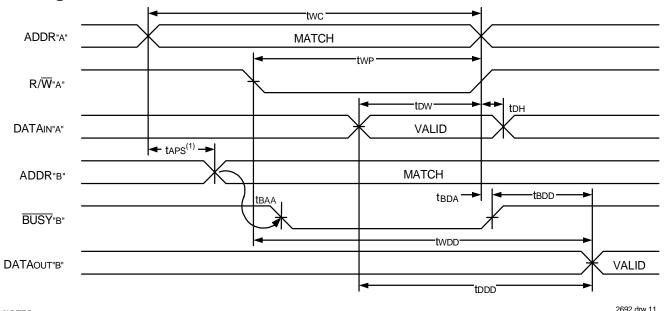
		7132X20 ⁽¹⁾ 7142X20 ⁽¹⁾ Com'l Only		7132X25 ⁽²⁾ 7142X25 ⁽²⁾ Com'l, Ind & Military		7132X35 7142X35 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
BUSY Timing	BUSY Timing (For Master IDT7132 Only)							
t BAA	BUSY Access Time from Address		20	—	20	_	20	ns
t BDA	BUSY Disable Time from Address		20		20	1	20	ns
t BAC	BUSY Access Time from Chip Enable		20		20	1	20	ns
tBDC	BUSY Disable Time from Chip Enable		20	_	20	1	20	ns
twdd	Write Pulse to Data Delay ⁽²⁾		50	_	50	-	60	ns
twн	Write Hold After BUSY ⁽⁶⁾	12	_	15	_	20	_	ns
todo	Write Data Valid to Read Data Delay ⁽²⁾		35	_	35	-	35	ns
taps	Arbitration Priority Set-up Time ⁽³⁾	5		5		5		ns
tBDD	BUSY Disable to Valid Data ⁽⁴⁾		25	-	35	-	35	ns
BUSY Timing (For Slave IDT7142 Only)								
twB	Write to BUSY Input ⁽⁵⁾	0		0		0		ns
twн	Write Hold After BUSY ⁽⁶⁾	12	_	15	_	20	_	ns
twdd	Write Pulse to Data Delay ⁽²⁾		40		50	-	60	ns
todo	Write Data Valid to Read Data Delay ⁽²⁾		30	_	35		35	ns

						2692 tbl 11a		
		7142 Con	2X55 2X55 n'l & tary	7132X100 7142X100 Com'l & Military				
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit		
BUSY Timing	BUSY Timing (For Master IDT7132 Only)							
t BAA	BUSY Access Time from Address		30		50	ns		
t BDA	BUSY Disable Time from Address	_	30	_	50	ns		
t BAC	BUSY Access Time from Chip Enable	_	30	_	50	ns		
tBDC	BUSY Disable Time from Chip Enable	_	30	_	50	ns		
twdd	Write Pulse to Data Delay ⁽²⁾	_	80	_	120	ns		
twн	Write Hold After BUSY ⁽⁶⁾	20	_	20		ns		
todd	Write Data Valid to Read Data Delay ⁽²⁾	_	55	_	100	ns		
taps	Arbitration Priority Set-up Time ⁽³⁾	5	_	5		ns		
tBDD	BUSY Disable to Valid Data ⁽⁴⁾	_	50	_	65	ns		
BUSY Timing (For Slave IDT7142 Only)								
twB	Write to BUSY Input ⁽⁵⁾	0		0		ns		
twн	Write Hold After BUSY ⁽⁶⁾	20		20		ns		
twdd	Write Pulse to Data Delay ⁽²⁾	_	80		120	ns		
todd	Write Data Valid to Read Data Delay ⁽²⁾		55		100	ns		

NOTES: 2692 tbl 11b

- 1. PLCC package only.
- 2. Port-to-port delay through RAM cells from the writing port to the reading port, refer to "Timing Waveform of Write with Port -to-Port Read and BUSY."
- 3. To ensure that the earlier of the two ports wins.
- 4. tbdd is a calculated parameter and is the greater of 0, twbd twp (actual) or tbdd tbw (actual).
- 5. To ensure that a write cycle is inhibited on port "B" during contention on port "A".
- 6. To ensure that a write cycle is completed on port "B" after contention on port "A".
- 7. 'X' in part numbers indicates power rating (SA or LA).
- 8. Industrial temperature: for specific speeds, packages and powers contact your sales office.

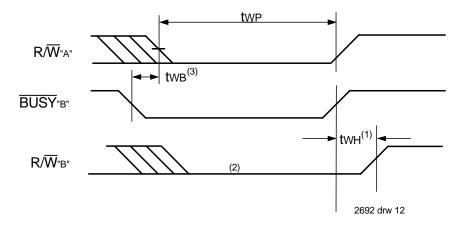
Timing Waveform of Write with Port-to-Port Read and **BUSY**(2,3,4)



NOTES:

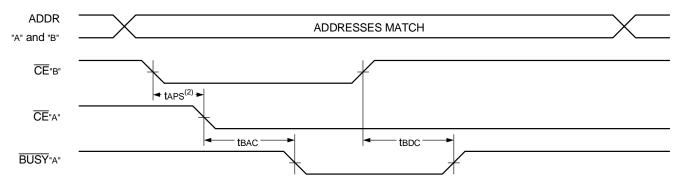
- 1. To ensure that the earlier of the two ports wins. taps is ignored for Slave (IDT7142).
- 2. $\overline{CE}_L = \overline{CE}_R = V_{IL}$
- 3. $\overline{OE} = V_{IL}$ for the reading port.
- 4. All timing is the same for the left and right ports. Port "A" may be either the left or right port. Port "B" is opposite from port "A".

Timing Waveform of Write with **BUSY**(4)



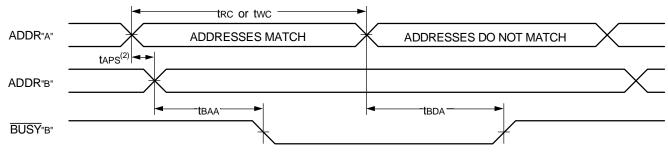
- 1. twn must be met for both BUSY Input (IDT7142, slave) or Output (IDT7132, master).
- 2. $\overline{\text{BUSY}}$ is asserted on port "B" blocking R/ $\overline{\text{W}}$ "B", until $\overline{\text{BUSY}}$ "B" goes HIGH.
- 3. twb applies only to the slave version (IDT7142).
- 4. All timing is the same for the left and right ports. Port 'A' may be either the left or right port. Port "B" is opposite from port "A".

Timing Waveform of **BUSY** Arbitration Controlled by **CE** Timing⁽¹⁾



2692 drw 13

Timing Waveform of $\overline{\textbf{BUSY}}$ Arbitration Controlled by Address Match Timing⁽¹⁾



2692 drw 14

NOTES

- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. If taps is not satisified, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted (7132 only).

Truth Tables

Table I. Non-Contention Read/Write Control⁽⁴⁾

Left or Right Port ⁽¹⁾				
R/W	ΖĒ	Œ	D0-7	Function
Х	Н	Х	Z	Port Disabled and in Power-Down Mode, ISB2 or ISB4
Х	Н	Х	Z	CER = CEL = VH, Power-Down Mode, ISB1 or ISB3
L	L	Χ	DATAIN	Data on Port Written into Memory ⁽²⁾
Н	L	L	DATAOUT	Data in Memory Output on Port ⁽³⁾
Х	L	Н	Z	High Impedance Outputs

2692 tbl 12

- 1. AOL A10L \neq AOR A10R
- 2. If $\overline{\text{BUSY}} = L$, data is not written.
- 3. If $\overline{BUSY} = L$, data may not be valid, see two and too timing.
- 4. 'H' = VIH, 'L' = VIL, 'X' = DON'T CARE, 'Z' = HIGH IMPEDANCE

Table II — Address **BUSY** Arbitration

Inputs			Out	puts	
CEL	CER	AOL-A10L AOR-A10R	BUS YL(1)	BUSY _R ⁽¹⁾	Function
Х	Χ	NO MATCH	Н	Н	Normal
Н	Χ	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES: 2692 tbl 13

- Pins BUSYL and BUSYR are both outputs for IDT7132 (master). Both are inputs for IDT7142 (slave). BUSYx outputs on the IDT7132 are open drain, not push-pull outputs. On slaves the BUSYx input internally inhibits writes.
- 'L' if the inputs to the opposite port were stable prior to the address and enable inputs
 of this port. 'H' if the inputs to the opposite port became stable after the address and
 enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR = LOW will
 result. BUSYL and BUSYR outputs can not be LOW simultaneously.
- Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

Functional Description

The IDT7132/IDT7142 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT7132/IDT7142 has an automatic power down feature controlled by $\overline{\text{CE}}$. The $\overline{\text{CE}}$ controls onchip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{\text{CE}}$ = VIH). When a port is enabled, access to the entire memory array is permitted.

Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The BUSY pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a busy indication, the write signal is gated internally to prevent the write from proceeding.

The use of \overline{BUSY} Logic is not required or desirable for all applications. In some cases it may be useful to logically OR the \overline{BUSY} outputs together and use any \overline{BUSY} indication as an interrupt source to flag the event of an illegal or illogical operation.

The \overline{BUSY} outputs on the IDT7132 RAM master are totem-pole type outputs and do not require pull-up resistors to operate. If these RAMs are being expanded in depth, then the \overline{BUSY} indication for the resulting array does not require the use of an external AND gate.

Width Expansion with Busy Logic Master/Slave Arrays

When expanding an SRAM array in width while using BUSY logic, one master part is used to decide which side of the SRAM array will receive a BUSY indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the BUSY signal as a write inhibit signal. Thus on the IDT7132/IDT7142 SRAMs the BUSY pin is an output if the part is Master (IDT7132), and the BUSY pin is an input if the part is a Slave (IDT7142) as shown in Figure 3.

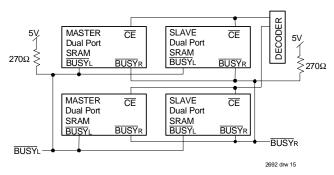
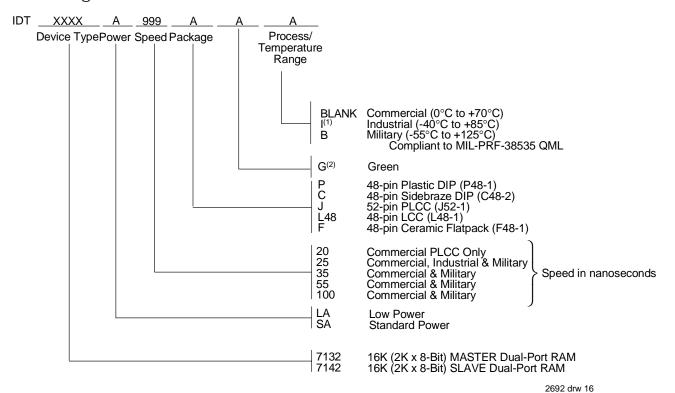


Figure 4. Busy and chip enable routing for both width and depth expansion with IDT7132 (Master) and (Slave) IDT7142 SRAMs.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating \overline{BUSY} on one side of the array and another master indicating \overline{BUSY} on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The \overline{BUSY} arbitration, on a Master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a \overline{BUSY} flag to be output from the master before the actual write pulse can be initiated with either the R/\overline{W} signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Ordering Information



NOTES:

- 1. Industrial temperature range is available. For specific speeds, packages and powers contact your sales office.
- 2. Green parts available. For specific speeds, packages and powers contact your local sales office.

Datasheet Document History

03/24/99:		Initiated datasheet document history
		Converted to new format
		Cosmetic and typographical corrections
	Pages 2 and 3	Added additional notes to pin configurations
06/08/99:		Changed drawing format
08/26/99:	Page 14	Changed Busy Logic and Width Expansion copy
11/10/99:	-	Replaced IDT logo
01/12/00:	Pages 1 and 2	Moved full "Description" to page 2 and adjusted page layouts
	Page 1	Added "(LAonly)" to paragraph
	Page 2	Fixed P48-1 body package description
	Page 3	Increased storage temperature parameters
	· ·	Clarified TA parameter
	Page 4	DC Electrical parameters—changed wording from "open" to "disabled"
	Page 6	Added asteriks to Figures 1 and 3 in drw 06
	Page 14	Corrected part numbers
	· ·	Changed ±500mV to 0mV in notes
		Datasheet Document History continued on page 16
	Page 3 Page 4 Page 6	Increased storage temperature parameters Clarified TA parameter DC Electrical parameters—changed wording from "open" to "disabled" Added asteriks to Figures 1 and 3 in drw 06 Corrected part numbers Changed ±500mV to 0mV in notes

Datasheet Document History (cont'd)

06/11/04:	Page 6 Page 4, 7, 9, 11 & 15	Corrected errors in Figure 3 by changing 1250 Ω to 270 Ω and removing "or Int" and Int Clarified Industrial temp offering for 25ns
	Page 5	Removed INT from Vol parameter in DC Electrical Characteristics table
	Page 6	Updated AC Test Conditions Input Rise/Fall Times from 5ns to 3ns
01/17/06:	Page 1	Added green availability to features
	Page 15	Added green indicator to ordering information
	Page 16	Replaced IDT address with new



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